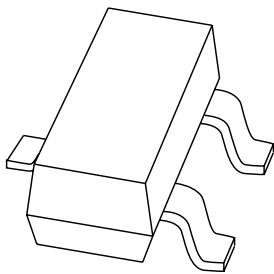


DATA SHEET



BCW31; BCW32; BCW33 NPN general purpose transistors

Product data sheet
Supersedes data of 2000 Jul 04

2004 Feb 06

NPN general purpose transistors

BCW31; BCW32; BCW33

FEATURES

- Low current (100 mA)
- Low voltage (32 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

NPN transistors in a plastic SOT23 package.
PNP complements: BCW29 and BCW30.

MARKING

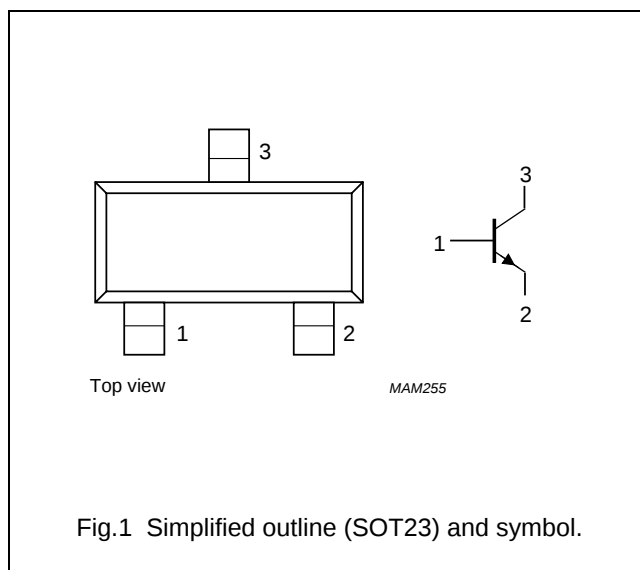
TYPE NUMBER	MARKING CODE ⁽¹⁾
BCW31	D1*
BCW32	D2*
BCW33	D3*

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.
* = W : Made in China.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BCW31	—	plastic surface mounted package; 3 leads	SOT23
BCW32			
BCW33			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CB0}	collector-base voltage	open emitter	—	32	V
V_{CEO}	collector-emitter voltage	open base; $I_C = 2\text{ mA}$	—	32	V
V_{EBO}	emitter-base voltage	open collector	—	5	V
I_C	collector current (DC)		—	100	mA
I_{CM}	peak collector current		—	200	mA
I_{BM}	peak base current		—	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	—	250	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

NPN general purpose transistors

BCW31; BCW32; BCW33

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 32\text{ V}$	–	–	100	nA
		$I_E = 0; V_{CB} = 32\text{ V}; T_j = 100\text{ °C}$	–	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$I_C = 10\text{ }\mu\text{A}; V_{CE} = 5\text{ V}$				
	BCW31		–	190	–	
	BCW32		–	330	–	
	BCW33		–	600	–	
	DC current gain	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$				
	BCW31		110	–	220	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	120	250	mV
		$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$	–	210	–	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	750	–	mV
		$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$	–	850	–	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	550	–	700	mV
C_c	collector capacitance	$I_E = I_c = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	2.5	–	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	–	–	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	–	–	10	dB

NPN general purpose transistors

BCW31; BCW32; BCW33

PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23

0 1 2 mm
scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT23		TO-236AB				04-11-04 06-03-16

NPN general purpose transistors

BCW31; BCW32; BCW33

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

1. Please consult the most recently issued document before initiating or completing a design.
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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

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